

GP 2814
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Dariusson

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

INOUE et al.

Serial Number: 09/473,988

Filed: December 29, 1999



Group Art Unit: 2814

Examiner: T. Doan

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

AMENDMENT

Director of Patents and Trademarks
Washington, D.C. 20231

December 6, 2000

Sir:

In response to the Office Action dated September 6, 2000, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 4, line 16, change "increases" to -increase-.

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IN THE CLAIMS:

Please cancel claim 10 without prejudice or disclaimer.

Please amend claims 1-3 and 7-9 as follows:

1. (Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film and including [an] first insulating layer of a composition containing SiN, and a second insulating layer formed on said first insulating layer.

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Handwritten signature or initials.